ABSTRACT OF THE DISCLOSURE

A mixture and method comprising same is described for chemical vibrational mechanical polishing (CVMP) of excess material from the underlying substrate surface. In one embodiment of the present invention, the method comprises: providing the substrate comprising the copper layer and the excess copper-containing material disposed thereupon; introducing the substrate into a vessel containing a chemical mechanical polishing mixture comprising a solution and a plurality of particles wherein the solution comprises an etchant, a modifier, and a surfactant and wherein an average particle diameter of the particles ranges from 100 to 3000 μm; and agitating the vessel with the substrate contained therein to remove the excess copper-containing material from the substrate.